

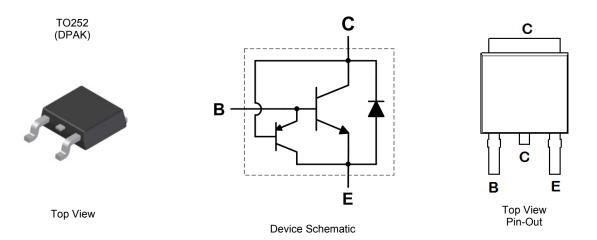
450V NPN HIGH VOLTAGE POWER TRANSISTOR IN TO252

Features

- BV_{CEO} > 450V
- BV_{CES} > 700V
- BV_{EBO} > 9V
- I_C = 1.5A high Continuous Collector Current
- Integrated Anti-Parallel Diode to act as free-wheeling diode
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.34 grams (approximate)



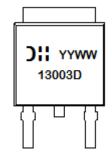
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXT13003DK-13	Standard	13003D	13	16	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



13003D = Product Type Marking Code **3!!** = Manufacturer's Code Marking

YYWW = Date Code Marking

YY = Last Digit of Year (ex: 14 = 2014)

WW = Week Code (01-53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage (V _{BE} = 0V)	V _{CES}	700	V
Collector-Emitter Voltage	V _{CEO}	450	V
Emitter-Base Voltage	V _{EBO}	9	V
Continuous Collector Current	I _C	1.5	Α
Peak Pulse Collector Current (Note 5)	I _{CM}	3	Α
Continuous Base Current	I _B	0.75	Α
Peak Pulse Base Current (Note 5)	I _{BM}	1.5	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)	- P _D	3.9	W	
Dowar Dissipation	(Note 7)		2.5		
Power Dissipation	(Note 8)		2.1		
	(Note 9)		1.6		
	(Note 6)		32		
Thermal Decistance Junction to Ambient Air	(Note 7)	$R_{\theta JA}$	51		
Thermal Resistance, Junction to Ambient Air	(Note 8)		59	°C/W	
	(Note 9)		80		
Thermal Resistance, Junction to Leads (Note 10)		$R_{ heta JL}$	3		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 11)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

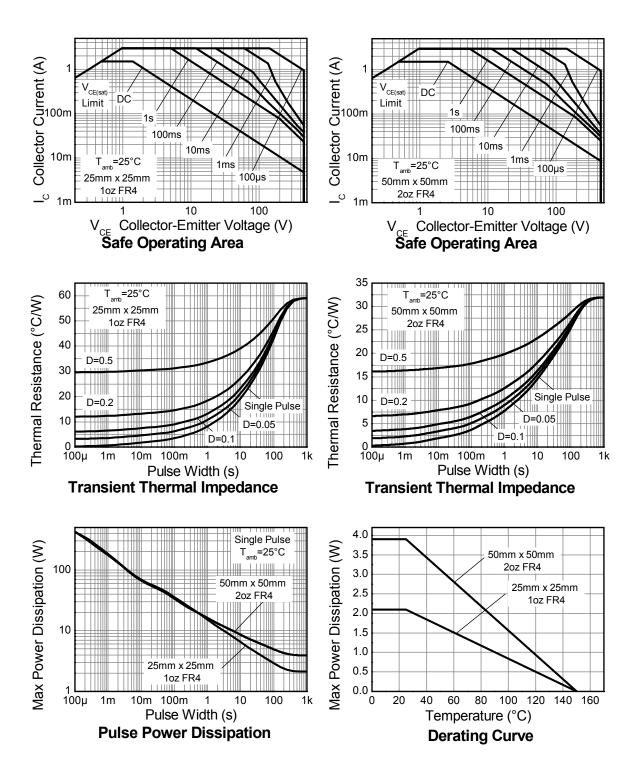
Notes:

- 5. Pulse test for pulse width < 5ms, duty cycle ≤ 10%.
 6. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as note (6), except the device is surface mounted on 25mm x 25mm 2oz copper. 8. Same as note (6), except the device is surface mounted on 25mm x 25mm 1oz copper.
- 9. Same as note (6), except mounted on minimum recommended pad (MRP) layout.
- 10. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

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Thermal Characteristics and Derating Information



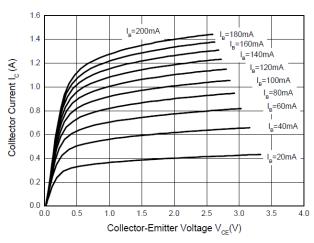


Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

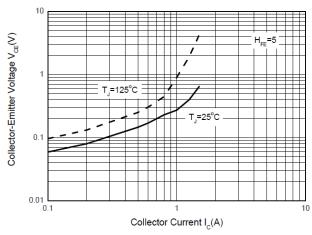
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Emitter Breakdown Voltage	BV _{CES}	700	_	_	V	I _C = 100μA, V _{BE} = 0V
Collector-Emitter Breakdown Voltage	BV _{CEO}	450	_	_	V	I _C = 100μA
Emitter-Base Breakdown Voltage	BV _{EBO}	9	_	_	V	I _E = 100μA
Collector Cutoff Current	I _{CEV}	1	_	10	μA	V _{CE} = 700V, V _{BE} = -1.5V
DC current transfer Static ratio (Note 12)	h _{FE}	20 16 5	1 1 1	40 30 25		I_C = 20mA, V_{CE} = 10V I_C = 0.5A, V_{CE} = 2V I_C = 1.0A, V_{CE} = 2V
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(sat)}	1 1	_	0.3 0.4	V	$I_C = 0.5A$, $I_B = 0.1A$ $I_C = 1A$, $I_B = 0.25A$
Base-Emitter Saturation Voltage (Note 12)	V _{BE(sat)}	1 1		1.0 1.2	V	$I_C = 0.5A$, $I_B = 0.1A$ $I_C = 1A$, $I_B = 0.25A$
Output Capacitance	C _{ob}	_	18	_	pF	V _{CB} = 10V, f = 0.1MHz
Transition Frequency	f _T	4	_	_	MHz	I _C = 0.1A, V _{CE} = 10V
Turn-on Time with Resistive Load	t _{on}	_	0.35	_		
Storage Time with Resistive Load	ts	_	2.31	_	μs	$I_C = 1A, V_{CC} = 125V, I_{B1} = 0.2A,$ $I_{B2} = -0.2A$
Fall Time with Resistive Load	t _f	_	0.21	_		IBS0.2A

Note:

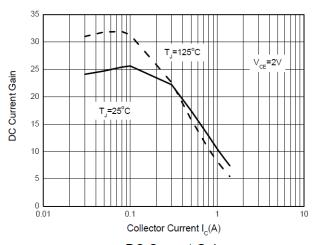
$\textbf{Typical Electrical Characteristics} \ (@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$



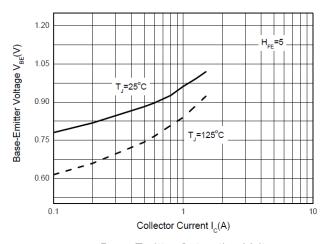




Collector-Emitter Saturation Region



DC Current Gain



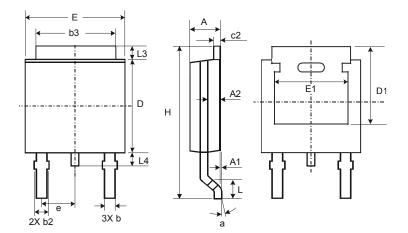
Base-Emitter Saturation Voltage

^{12.} Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



Package Outline Dimensions

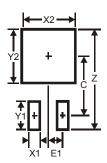
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



TO252						
Dim	Dim Min		Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
c2	0.45	0.58	0.531			
D 6.00		6.20	6.10			
D1	5.21	_	_			
е	_	_	2.286			
Е	6.45	6.70	6.58			
E1	4.32	_	_			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	_			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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